



*Emall*  
Attorney's Docket No. 5308-156

*28118*  
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
In re: Ryu et al.  
Serial No.: 09/911,995  
Filed: July 24, 2001

Group Art Unit: 2811  
Confirmation No.: 5240  
Examiner: Gene M. Munson

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD  
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND  
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE  
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A  
SHORTING CHANNEL

Date: January 20, 2004

Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

Please find attached a check in the amount of \$180.00 for the fee specified in 37 C.F.R. § 1.17(p). The Commissioner is authorized to charge any additional fee or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

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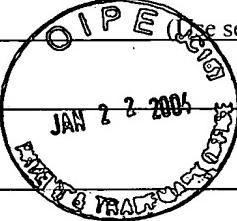
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*Ban Younan*  
Ban Younan

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-156			Serial No. 09/911,995
LIST OF DOCUMENTS CITED BY APPLICANT  <i>(use several sheets if necessary)</i>							
				Applicants: Ryu et al.			
				Filing Date: July 24, 2001			Group 2811
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
1		5,479,316	12/26/95	Smrtic et al.	361	322	
2		5,739,564	04/14/98	Kosa et al.	257	298	
3		6,228,720	05/08/01	Kitabatake et al.	438	268	
4		6,239,463	05/29/01	Williams et al.	257	328	
5		6,316,791	11/13/01	Schörner et al.	257	77	
6		6,593,620	07/15/03	Hshieh et al.	257	335	
7		6,610,366	08/26/03	Lipkin	427	378	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
8		WO98/02924	01/22/98	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
9	Dimitrijev et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.						
10	De Mao et al., "Thermal Oxidation of SiC in N <sub>2</sub> O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.						
11	Ryu et al., Article and Presentation: "27 mΩ-cm <sup>2</sup> , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices &amp; ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.						
12	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> . pp. 119-120.						
13	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> . Vol. 11, No. 4, Jul/Aug 1993, pp. 1533-40.						

EXAMINER \_\_\_\_\_ DATE CONSIDERED  
 \*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.